

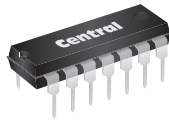
MPQ7093
SILICON
HIGH VOLTAGE
QUAD PNP TRANSISTOR



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR MPQ7093 is comprised of four independent PNP silicon transistors mounted in a 14-pin DIP, designed for high voltage amplifier applications.



TO-116 CASE

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Collector-Base Voltage	V_{CBO}	250	V
Collector-Emitter Voltage	V_{CEO}	250	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Continuous Collector Current	I_C	500	mA
Power Dissipation (per transistor)	P_D	750	mW
Power Dissipation (total package)	P_D	1700	mW
Power Dissipation ($T_C=25^\circ\text{C}$) (total package)	P_D	3.0	W
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$

SYMBOL		UNITS
V_{CBO}	250	V
V_{CEO}	250	V
V_{EBO}	5.0	V
I_C	500	mA
P_D	750	mW
P_D	1700	mW
P_D	3.0	W
T_J, T_{stg}	-65 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS PER TRANSISTOR: ($T_A=25^\circ\text{C}$)

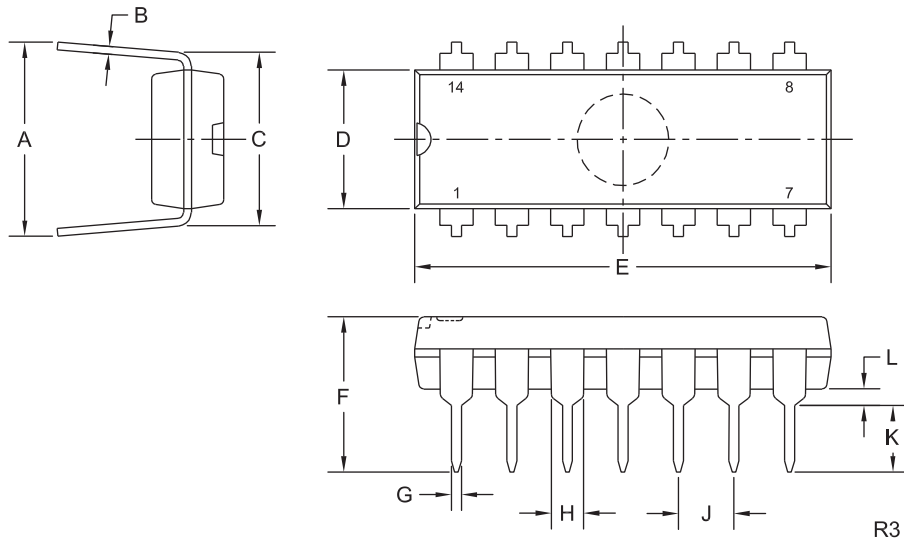
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{CBO}	$V_{CB}=180\text{V}$			250	nA
I_{EBO}	$V_{EB}=3.0\text{V}$			100	nA
BV_{CBO}	$I_C=100\mu\text{A}$	250			V
BV_{CEO}	$I_C=1.0\text{mA}$	250			V
BV_{EBO}	$I_E=100\mu\text{A}$	5.0			V
$V_{CE(SAT)}$	$I_C=20\text{mA}, I_B=2.0\text{mA}$			0.5	V
$V_{BE(SAT)}$	$I_C=20\text{mA}, I_B=2.0\text{mA}$			0.9	V
h_{FE}	$V_{CE}=10\text{V}, I_C=1.0\text{mA}$	25			
h_{FE}	$V_{CE}=10\text{V}, I_C=10\text{mA}$	35			
h_{FE}	$V_{CE}=10\text{V}, I_C=30\text{mA}$	25			
f_T	$V_{CE}=20\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	50			MHz
C_{ob}	$V_{CB}=20\text{V}, I_E=0, f=1.0\text{MHz}$			5.0	pF
C_{ib}	$V_{EB}=3.0\text{V}, I_C=0, f=1.0\text{MHz}$			75	pF

R0 (14-June 2013)

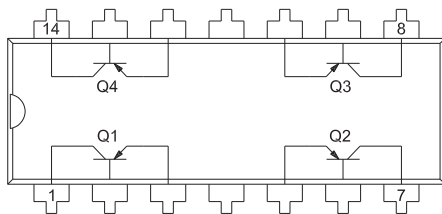
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TO-116 CASE - MECHANICAL OUTLINE



PIN CONFIGURATION



LEAD CODE:

- | | |
|------------------|-------------------|
| 1) Collector Q1 | 8) Collector Q3 |
| 2) Base Q1 | 9) Base Q3 |
| 3) Emitter Q1 | 10) Emitter Q3 |
| 4) No Connection | 11) No Connection |
| 5) Emitter Q2 | 12) Emitter Q4 |
| 6) Base Q2 | 13) Base Q4 |
| 7) Collector Q2 | 14) Collector Q4 |

MARKING: FULL PART NUMBER

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.310	0.390	7.9	9.9
B	0.008	0.014	0.2	0.4
C	0.310		7.9	
D	0.240	0.260	6.1	6.6
E	0.740	0.760	18.8	19.3
F	-	0.300	-	7.6
G	0.014	0.022	0.4	0.6
H	0.050		1.3	
J	0.100		2.5	
K	0.125	0.150	3.2	3.8
L	0.015	-	0.4	-

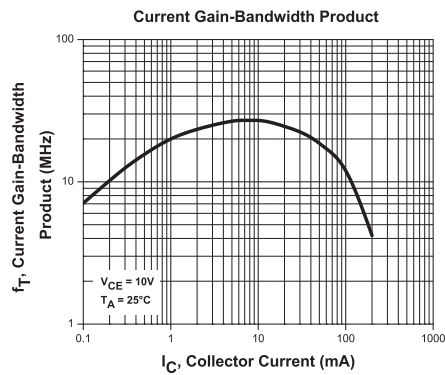
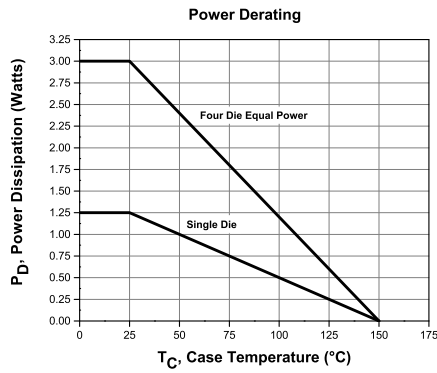
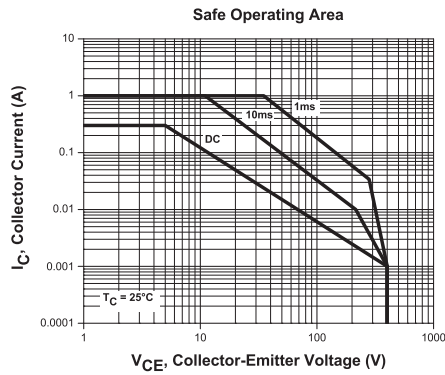
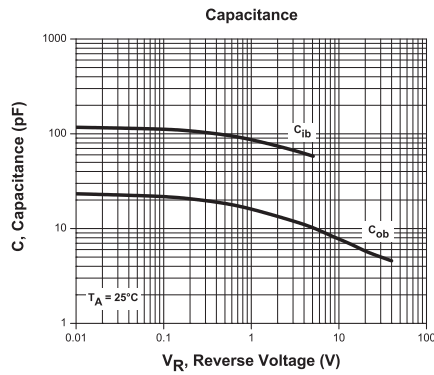
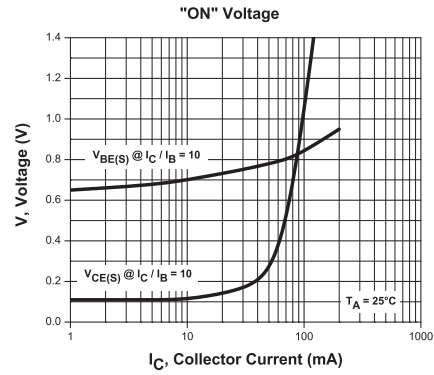
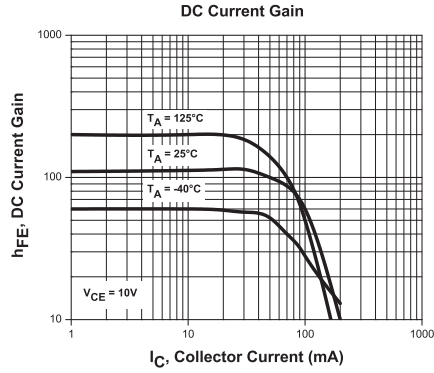
TO-116 (REV: R3)

R0 (14-June 2013)

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TYPICAL ELECTRICAL CHARACTERISTICS



R0 (14-June 2013)